Compact - IPM ID20FFX60U1S

Features

- UL 1557 Certified.
- Adopt the latest trench IGBT technology to get a good overall loss trade-off.
- Open Emitter on N terminal for low cost current sensing application.
- Match propagation delay and arm shooting through prevention.
- Built-in bootstrap diodes with current limiting resistor.
- Provide a fault signal (FO pin) and shut-off internal IGBT when suffer S.C. and under-voltage faulty event.
- · RoHS compatible.

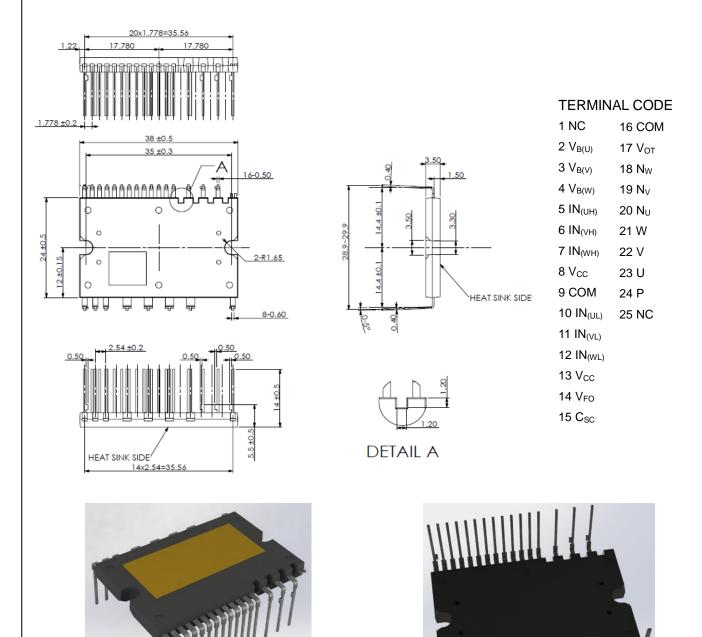
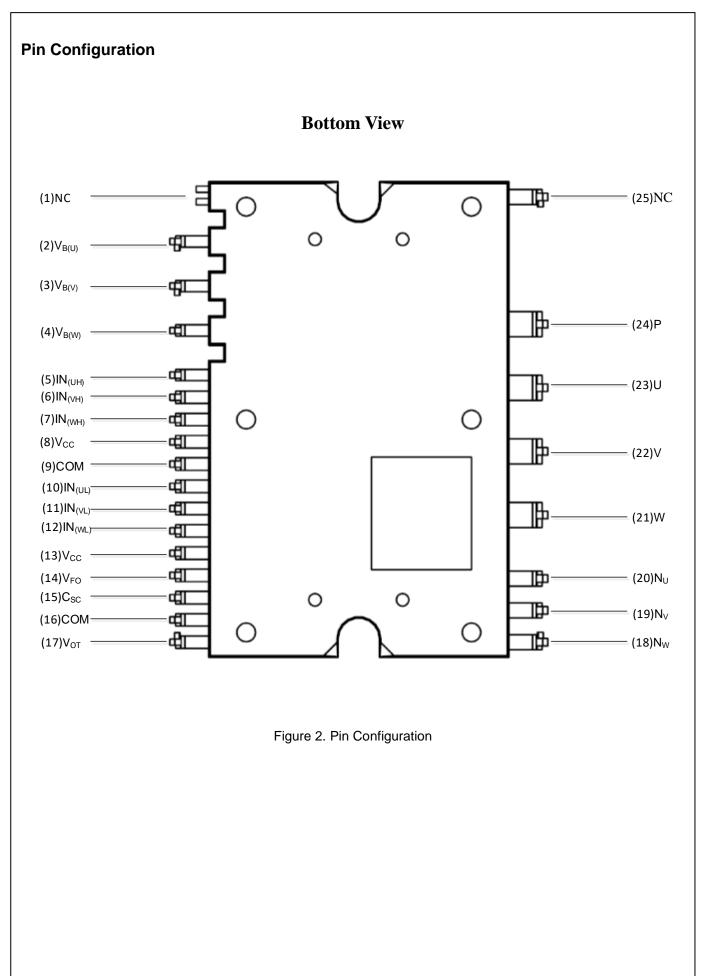


Table1: Pin Descriptions

No.	Symbol	Pin Description
1	NC	No Connection
2	$V_{B(U)}$	High - side Bias Voltage for U Phase IGBT Driving
3	$V_{B(V)}$	High - side Bias Voltage for V Phase IGBT Driving
4	$V_{B(W)}$	High - side Bias Voltage for W Phase IGBT Driving
5	IN _(UH)	Signal Input Terminal for High-side U Phase
6	IN _(VH)	Signal Input Terminal for High-side V Phase
7	IN _(WH)	Signal Input Terminal for High-side W Phase
8	V _{CC}	Supply Voltage Terminal for Driver IC
9	СОМ	Reference Voltage Terminal for Driver IC
10	IN _(UL)	Signal Input Terminal for Low-side U Phase
11	IN _(VL)	Signal Input Terminal for Low-side V Phase
12	IN _(WL)	Signal Input Terminal for Low-side W Phase
13	Vcc	Supply Voltage Terminal for Driver IC
14	V_{FO}	Fault Output Terminal
15	Csc	Short-Current Detection Input
16	СОМ	Reference Voltage Terminal for Driver IC
17	V_{OT}	Temperature output
18	N_{W}	Negative DC-Link Input Terminal for W Phase
19	N _V	Negative DC-Link Input Terminal for V Phase
20	N _U	Negative DC-Link Input Terminal for U Phase
21	W	Output Terminal for W Phase
22	V	Output Terminal for V Phase
23	U	Output Terminal for U Phase
24	Р	Positive DC – Link Input
25	NC	No Connection

(see figure 2, next page)



The IPM Internal Block Diagram 2 3 $V_{B(W)}$ 24 23 8 $V_{CC} \\$ 5 6 IN_(VH) 7 IN_{(WF} Signal 22 10 Input IN_{(UL} 11 IN_{(VL} 12 IN_(WL) 21 W Gate 14 V_{FO} Driver Fault Circuit Logic Nυ 20 V_{CC} 13 Protection Csc 15 Circuit 17 V_{OT} 19 Supply 9/16 COM Circuit Nw 18

Figure 3. IPM Internal Block Diagram

Application:

- Short-circuit current protection AC 100~240Vrms class 3 phase output for low power motor control.
- Household electric appliances such as air conditioners, washing machines, refrigerators, etc...
- Low power industrial servo drives applications such as sewing machine, treadmill, etc...

MAXIMUM RATINGS $(T_j = 25^{\circ}C)$

INVERTER PART

Item	Symbol	Min.	Max.	Unit
Between collector to emitter voltage	V _{CES} (IGBT)	•	600	V
Supply voltage P-N	V_{PN}	•	450	V
Supply voltage (surge) P-N	V _{PN (surge)}	ı	500	V
Each IGBT collector current	± I _C (Tc = 25°C)	-	20	Α
Each IGBT collector current	± I _C (Tc = 90°C)	•	16	Α
Each IGBT collector current (peak)	\pm ICP (Tc = 25 °C, T $_{\rm j}$ $<$ 150 °C, Under 1ms Pulse Width)	1	40	Α
Collector dissipation	P_C (Tc = 25°C, per one chip)	-	70	W
Junction temperature	Tj (Note 1)	-	+150	$^{\circ}$

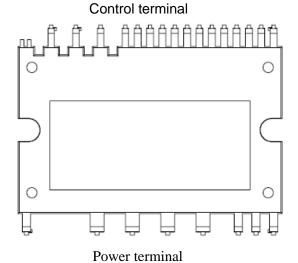
Note 1: Power chip in IPM is qualified for 175°C operation. But overall junction temperature should be limited by $T_j \le 125$ °C (@ $Tc \le 100$ °C) to fit long term reliability requirement.

CONTROL PART

Item	Symbol	Min.	Max.	Unit
Driver IC supply voltage	V _{CC}	-0.3	20	V
P - side floating supply voltage	$V_{B(u)S(u), B(V)S(V), B(W)S(W)}$	-0.3	20	V
Current sensing input voltage	V _{SC}	-0.3	Vcc+0.3	V
Logic input voltage	$\begin{split} & IN_{(UH)}, IN_{(VH)}, IN_{(WH)}, \\ & IN_{(UL)}, IN_{(VL)}, IN_{(WL)} \end{split}$	-0.3	Vcc+0.3	V
Fault output voltage	V _{FO}	-0.3	Vcc+0.3	V
Fault output current	I _{FO}	-	1	mA

TOTAL SYSTEM

Item	Symbol	Min.	Max.	Unit
Module case operating temperature	T _C	-20	+100	$^{\circ}$
Storage temperature	T_{stg}	-40	+125	$^{\circ}$
Isolation voltage (60Hz Sinusoidal, AC 1 minute, pins to heat-sink plate)	V_{iso}	1	1500	Vrms



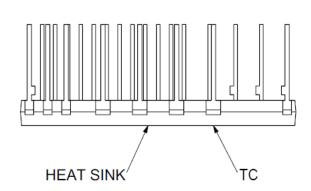


Figure 4. Tc Measurement Point

THERMAL RESISTANCE

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Junction to case thermal	$R_{th(j-c)Q}$	IGBT part (1/6)	-	1.8	-	°C AA/
resistance	R _{th(j-c)F}	FWD part (1/6)	-	2.2	-	°C∕W

ELECTRICAL CHARACTERISTICS $(T_j = 25^{\circ}C)$

INVERTER PART

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Collector-emitter saturation voltage	V _{CE (sat)}	$V_{CC} = V_{B(U)S(U), B(V)S(V), B(W)S(W)} = 15V, I_C = 20A, V_{SC} = 0V$ $T_{j=25^{\circ}C}$	ı	1.57	-	V
FWD forward voltage drop	V _F	$T_j = 25^{\circ}C$, - $I_C = 20A$	1	1.54	-	V
	T _{on}	$V_D = 300V$,	-	0.70	-	
Switching times	T _{c(on)}	$V_{CC} = V_{B(U), B(V), B(W)} = 15V,$	1	0.20	-	
(Fig. 5)	T _{off}	$I_C = 20A, T_j = 25^{\circ}C,$	1	0.90	-	μs
(i ig. 3)	$T_{c(off)}$	$V_{IN} = 5V <> 0V,$	-	0.15	-	
	T _{rr}	$V_{SC} = 0V$, Inductive Load	-	0.20	-	
Collector-emitter cut-off current	I _{CES}	V _{CE} =V _{CES}	-	-	500	μA

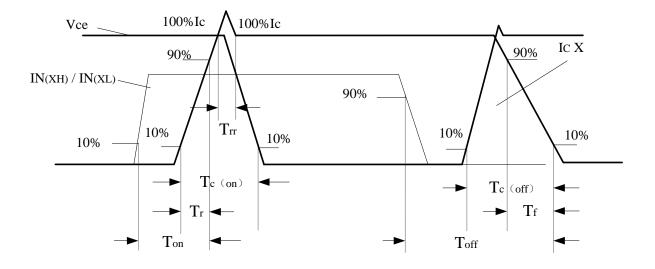


Figure 5. Switching Time Definition

CONTROL PART $(T_j = 25^{\circ}C)$						
Item	Symbol	Condition	Min.	Тур.	Max.	Unit
IN _(UH、VH、WH) , IN _(UL、VL、WL) ON threshold voltage	$V_{\text{th(on)}}$		-	2.0	2.4	V
IN _(UH、VH、WH) ,IN _(UL、VL、WL) OFF threshold voltage	$V_{\text{th(off)}}$		0.8	1.1	-	V
IN input bigg gurrent	In(uh. vh. wh)(HI)	VIN(UH, VH, WH) = 5V	0.7	1.0	1.5	mA
IN _(UH、VH、WH) input bias current	I _{IN(UH} , VH, WH) (LO)	$V_{IN(UH, VH, WH)} = 0V$	•	0	-	IIIA
IN input bigg ourrent	I _{IN(UL} , VL, WL) (HI)	$V_{IN(UL, VL, WL)} = 5V$	0.7	1.0	1.3	mA
IN _(UL、VL、WL) input bias current	I _{IN(UL} , VL, WL) (LO)	$V_{IN(UL, VL, WL)} = 0V$	-	0	-	ША
Driver IC supply voltage	V_{CC}		13.5	15.0	16.5	V
P - side floating supply voltage	$V_{B(U),\;B(V),\;B(W)}$		13.5	15.0	16.5	V
V _{CC} terminal input current	Ic		1	-	2.3	mΑ
Foult output voltage	V_{FOH}	$V_{SC} = 0V$ (Note 2)	4.9	-	-	V
Fault output voltage	V_{FOL}	V _{SC} =1V	-	-	950	mV
Short circuit trip level	$V_{SC(ref)}$	V _{CC} =15V, T _j = 25°C	0.455	0.480	0.505	V
Fault output pulse width	t _{FOD}		20	65	-	us
N side supply sireuit under veltage	UVT _{VCC}	Trip level	9.5	10.4	11.0	V
N-side supply circuit under voltage protection	UVR _{VCC}	Reset level	11.0	12.0	12.8	V
protection	UVH	Hysteresis	-	1.6	-	V
P-side supply circuit under voltage	UVT_Vb	Trip level	9.5	10.4	11.0	V
	UVR_{Vb}	Reset level	11.0	12.0	12.8	V
protection	UVH	Hysteresis	-	1.6	-	V
IN _(UL, VL, WL) Input filter time	t _{IN,FIL}	VIN = 0 & 5V (Note 3)	100	200	-	ns

Note 2: V_{FO} output is open collector type, so this signal line should be pulled up to the +5V power supply with approximately 4.7K Ω **Note 3:** For high side PWM, IN(UH, VH, WH) pulse width must be ≥ 1 us.

 V_{OT}

Bootstrap diode

forward voltage

Limiting resistance

LVIC temperature=90°C

LVIC temperature=25°C

If=10mA, $T_i = 25^{\circ}C$

Individual resistor

Input Filter Function

Temperature Output

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R

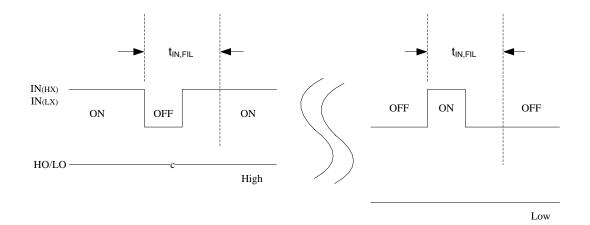


Figure 6. Input Filter Function

2.77

1.13

25

0.8

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Ohm

1.1

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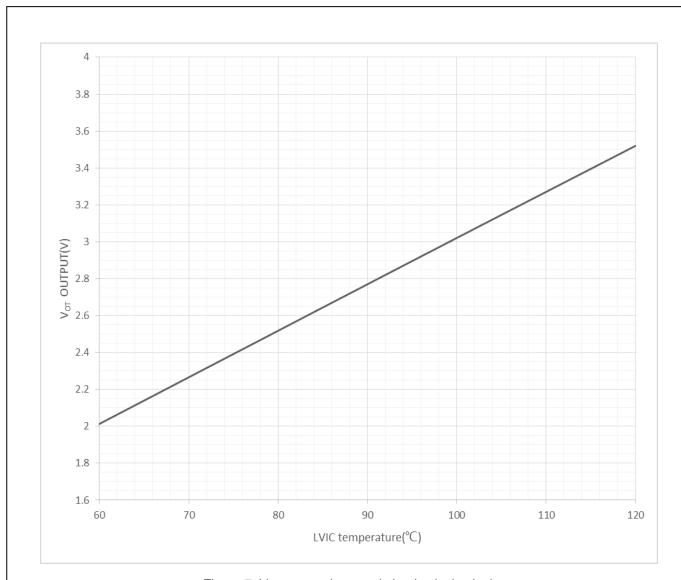


Figure 7. V_{OT} output characteristics (typical value)

RECOMMENDED OPERATION CONDITIONS

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
DC – Link Supply voltage	V_D	Applied between P-N	0	400	450	V
Driver IC supply voltage	V_{CC}	Applied between V _{CC} - COM	13.5	15.0	16.5	V
P - side floating supply voltage	V_{BS}	Applied between $V_{B(u \cdot v \cdot w)} - V_{S(u \cdot v \cdot w)}$	13.5	15.0	16.5	V
Input ON threshold voltage	V _{sc(ON)}	Applied between IN(UH, VH, WH) - COM	0 ~ 0.65		V	
Input OFF threshold voltage	$V_{\text{sc}(OFF)}$	and IN _(UL、VL、WL) - COM	4.0 ~ 5.5		V	
Supply voltage ripple	ΔV_D , ΔV_{DB}		-1	-	1	V/µs
Arm shoot-through blocking time	t _{dead}		1	-		μs
PWM input frequency	f _{PWM}	$T_C \leq 100^{\circ}C$, $T_j \leq 125^{\circ}C$	-	15	-	kHz

MECHANICAL CHARACTERISTICS AND RATINGS

Item	Condition			Тур.	Max.	Unit
Mounting torque	Mounting screw: M3	Recommended 0.65N•m	0.60	0.65	0.70	N•m
Weight			-	9.5	-	g
Heat-sink flatness			-50	-	100	μm

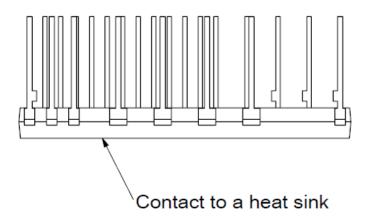


Figure 8. Measurement Location of Heat-sink Flatness

Input/Output Timing Diagram IN(XH) IN(XL) Vsc V_{FO} Но и, v, w Lo u,v,w Figure 9. Input/Output Timing Diagram DC Bus H_{O} IN(XH)(5,6,7)Vsc IN(XL) U,V,W IN(xH) DC Bus 0 0 U,V,W0 0 0 0 0 0 0 Driver IC 0 DC Bus (23,22,21)0 IN(xL) L_{O} (X=U,V,W)(10,11,12) Figure 10. Input/Output Signal Circuit



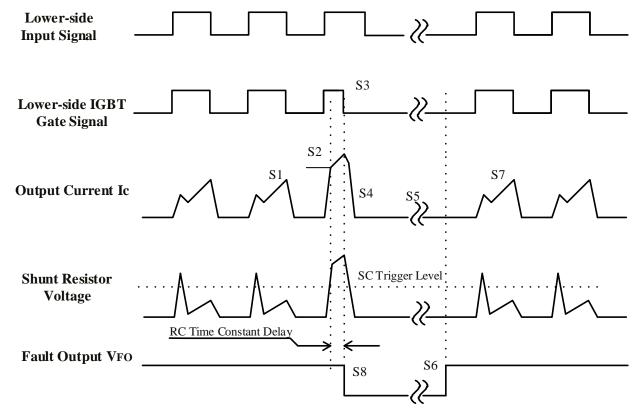


Figure 11. Timing Chart of SC Operation

- S1. The Lower-side IGBT's are controlled by input PWM signal.(Normal operation)
- S2. Short circuit event occurs and reaches the limited level. (SC protection is trigger.)
- S3. All N-side IGBT gate driving signals are disabled.
- S4. Current is cut off caused by IGBT turns OFF.
- S5. Disabled state.
- S6. Fo finishes output, but IGBT of each phase returns to normal state until inputting next ON signal(L→H).
- S7. IGBT returns for normal operation when fault state is reset.
- S8. Fault output starts once SC protection is trigger.

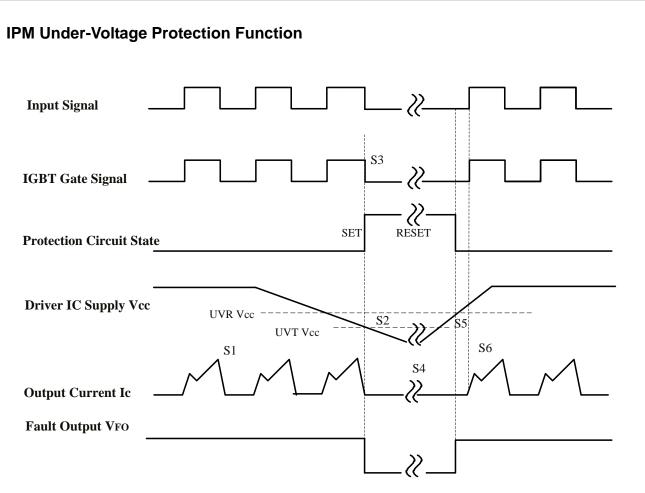


Figure 12. Timing Chart of Under-Voltage Operation

- S1. The IGBT's are controlled by input PWM signal.(Normal operation)
- S2. Under-voltage protection is trigger.
- S3. IGBT driving signals are disabled when fault condition occur.
- S4. Fault state and the period will be able to control by external capacitor value.
- S5. Under-voltage event is recovered.
- S6. IGBT returns for normal operation when fault state is reset.

Direct Input (without Photo Coupler) Interface Example

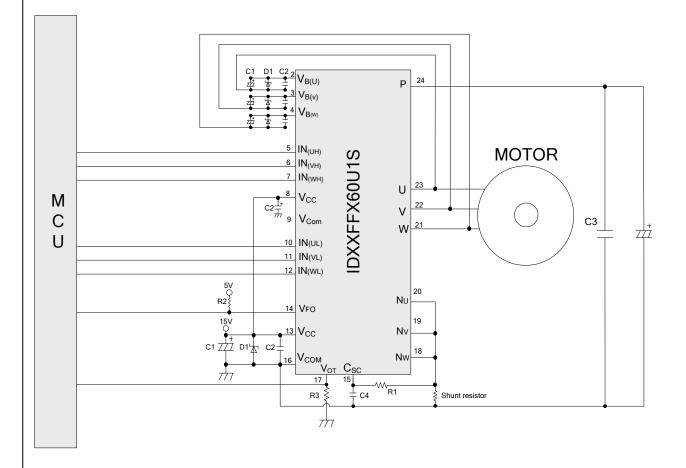
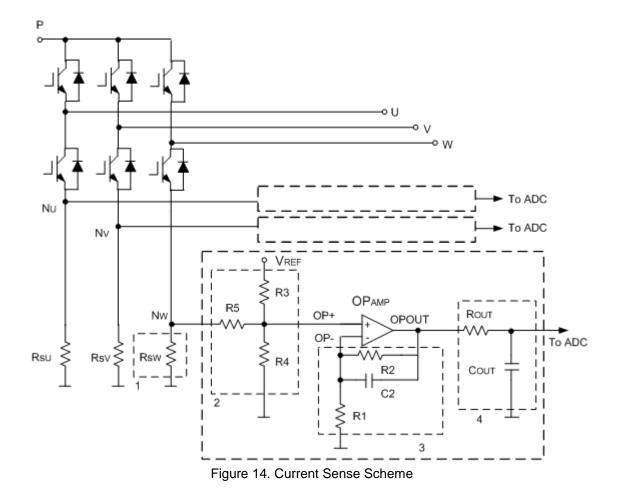


Figure 13. Typical Application Circuit Interface Example without Photo-Coupler

Design reference:

- 1. $R1:100\Omega$
- 2. R2 : $4.7K\Omega$ (VFO output is open collector so to have a pull high resistor is needed.)
- 3. R3: 5k-200k pull down resistor for getting linear output characteristics at low temperature below room temperature.
 - 4. $C1:10 \sim 100 \mu F$ (Electrolytic, low impendence)
- 5. C2: 100 ~ 1000pF (Ceramic) (The capacitor could filter the noise, but should be careful to the dead time)
- 6. C3: 220µF (Electrolytic, low impendence)
- 7. D1: Zener diode (It is recommended to insert a Zener diode to prevent gate lifting and surge destruction)
- 8. Only connect either pin 9 or pin 16 to ground, do not connect both together to form the ground loop internally.

Current Sense Scheme



Description:

- 1. Half-bridge current sensing
- 2. Voltage shifting of the $\ensuremath{V_{\text{sense}}}$
- 3. Voltage gain and filtering
- 4. Capacitor required by the ADC for sampling purpose

 R_{OUT} resistor is usually required in order to make the OP_{AMP} stable when the C_{OUT} capacitance increases

Design Reference:

1. R1 : 1.0 KΩ 2. R2 : 5.6 KΩ 3. R3 : 4.7 KΩ

4. R4: 910 Ω 5. R5 : 910 Ω 6.ROUT : 1.0 ΚΩ

7. C2:10pF (Ceramic)

Precautions on Electrostatic Electricity

(1) Operators must wear anti-static clothing and conductive shoes (or a leg or heel strap).

- (2) Operators must wear a wrist strap grounded to earth via a resistor of about 1 $M\Omega$.
- (3) Soldering irons must be grounded from iron tip to earth, and must be used only at low voltages.
- (4) If the tweezers you use are likely to touch the device terminals, use anti-static tweezers and in particular avoid metallic tweezers. If a charged device touches a low-resistance tool, rapid discharge can occur. When using vacuum tweezers, attach a conductive chucking pat to the tip, and connect it to a dedicated ground used especially for anti-static purposes (suggested resistance value: 10^4 to $10^8\Omega$).
- (5) Do not place devices or their containers near sources of strong electrical fields (such as above a CRT).
- (6) When storing printed circuit boards which have devices mounted on them, use a board container or bag that's protected against static charge. To avoid the occurrence of static charge or discharge due to friction, keep the boards separate from one other and do not stack them directly on top of one another.
- (7) Ensure, if possible, that any articles (such as clipboards) which are brought to any location where the level of static electricity must be closely controlled are constructed of anti-static materials.
- (8) In cases where the human body comes into direct contact with a device, be sure to wear anti-static finger covers or gloves (suggested resistance value: $10^8\Omega$ or less).
- (9) Equipment safety covers installed near devices should have resistance ratings of $10^9\Omega$ or less.
- (10) If a wrist strap cannot be used for some reason, and there is a possibility of imparting friction to devices, use an ionizer.

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